# TOSHIBA

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7MZ4051FK,TC7MZ4052FK,TC7MZ4053FK

TC7MZ4051FK 8-Channel Analog Multiplexer/Demultiplexer TC7MZ4052FK Dual 4-Channel Analog Multiplexer/Demultiplexer TC7MZ4053FK Triple 2-Channel Analog

Multiplexer/Demultiplexer

The TC7MZ4051/4052/4053FK are high-speed, low-voltage drive analog multiplexer/demultiplexers using silicon gate CMOS technology. In 3 V and 5 V systems these can achieve high-speed operation with the low power dissipation that is a feature of CMOS.

The TC7MZ4051/4052/4053FK offer analog/digital signal selection as well as mixed signals. The 4051 has an 8-channel configuration, the 4052 has an 4-channel × 2 configuration, and the 4053 has a 2-channel × 3 configuration.

The switches for each channel are turned ON by the control pin digital signals.

Although the control signal logical amplitude ( $V_{CC}$  – GND) is small, the device can perform large-amplitude ( $V_{CC}$  –  $V_{EE}$ ) signal switching.

For example, if  $V_{CC} = 3 \text{ V}$ , GND = 0 V, and  $V_{EE} = -3 \text{ V}$ , signals between -3 V and +3 V can be switched from the logical circuit using a single 3 V power supply.

All input pins are equipped with a newly developed input protection circuit that avoids the need for a diode on the plus side (forward side from the input to the V<sub>CC</sub>). As a result, for example, 5 V signals can be permitted on the inputs even when the power supply voltage to the circuits is off. As a result of this input power protection, the TC7MZ4051/4052/4053FK can be used in a variety of applications, including in the system which has two power supplies, and in battery backup circuits.

### Features

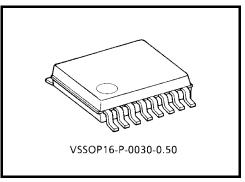
• Low ON resistance:  $R_{on} = 22 \Omega$  (typ.) ( $V_{CC} - V_{EE} = 3 V$ )

 $R_{on} = 15 \ \Omega \ (typ.) \ (V_{CC} - V_{EE} = 6 \ V)$ 

- High speed:  $t_{pd} = 3 \text{ ns} (typ.) (V_{CC} = 3.0 \text{ V})$
- Low power dissipation:  $I_{CC} = 4 \ \mu A \ (max) \ (Ta = 25^{\circ}C)$
- Input level:  $V_{IL} = 0.8 V (max) (V_{CC} = 3 V)$

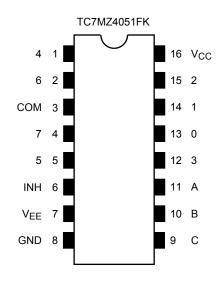
$$V_{IH} = 2.0 V (min) (V_{CC} = 3 V)$$

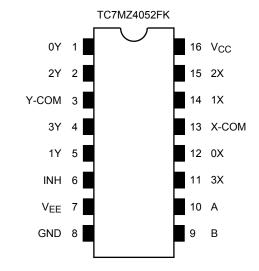
- Power down protection is provided on all control inputs
- Pin and function compatible with 74HC4051/4052/4053

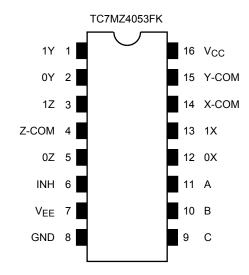


Weight: 0.02 g (typ.)

## Pin Assignment (top view)







## **Truth Table**

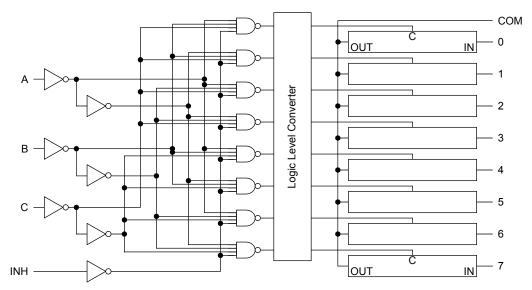
	Contro	l Inputs		"ON" Channel				
Inhibit	C*	В	А	MZ4051FK	MZ4052FK	MZ4053FK		
L	L	L	L	0	0X, 0Y	0X, 0Y, 0Z		
L	L	L	Н	1	1X, 1Y	1X, 0Y, 0Z		
L	L	Н	L	2	2X, 2Y	0X, 1Y, 0Z		
L	L	Н	Н	3	3X, 3Y	1X, 1Y, 0Z		
L	Н	L	L	4	—	0X, 0Y, 1Z		
L	Н	L	Н	5	—	1X, 0Y, 1Z		
L	Н	Н	L	6	—	0X, 1Y, 1Z		
L	Н	Н	Н	7	—	1X, 1Y, 1Z		
Н	Х	Х	Х	None	None	None		

X: Don't care, \*: Except MZ4052FK

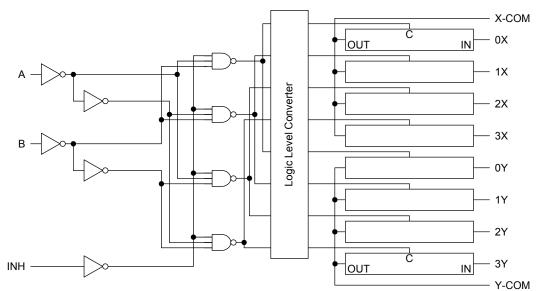
# **TOSHIBA**

### System Diagram

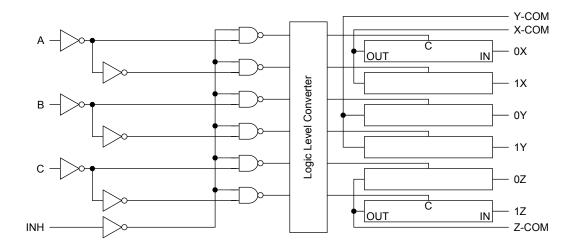
#### TC7MZ4051FK



#### TC7MZ4052FK



#### TC7MZ4053FK



#### Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V <sub>CC</sub>	-0.5~7.0	V	
Fower supply voltage	V <sub>CC</sub> ~V <sub>EE</sub>	-0.5~7.0		
Control input voltage	V <sub>IN</sub>	-0.5~7.0	V	
Switch I/O voltage	V <sub>I/O</sub>	$V_{EE} - 0.5  V_{CC} + 0.5$	V	
Input diode current	I <sub>IK</sub>	-20	mA	
I/O diode current	liok	±20	mA	
Switch through current	Ι <sub>Τ</sub>	±25	mA	
DC V <sub>CC</sub> or ground current	ICC	±50	mA	
Power dissipation	PD	180	mW	
Storage temperature	T <sub>stg</sub>	-65~150	°C	

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Operating Ranges (Note)**

Characteristics	Symbol	Rating	Unit
	V <sub>CC</sub>	2~6	
Power supply voltage	V <sub>EE</sub>	-4~0	V
	V <sub>CC</sub> ~V <sub>EE</sub>	2~6	
Input voltage	V <sub>IN</sub>	0~6.0	V
Switch I/O voltage	V <sub>I/O</sub>	V <sub>EE</sub> ~V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	0~100 (V_{CC} = 3.3 $\pm$ 0.3 V)	ns/V
input rise and fair time	avav	0~20 (V <sub>CC</sub> = 5 $\pm$ 0.5 V)	ns/V

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused control inputs must be tied to either  $V_{CC}$  or GND.

#### **Electrical Characteristics**

#### **DC Electrical Characteristics**

Characteristics		Symbol Test Condition				-	Ta = 25°0	C	Ta = -4	Ta = -40~85°C	
Characte			Test Condition	$V_{\text{EE}}(V)$	$V_{CC}\left(V\right)$	Min	Тур.	Max	Min	Max	Unit
					2.0	1.5			1.5		
	High-level	VIH			3.0	2.0	_	_	2.0	_	
	i ligii-level	۷IH			4.5	3.15	_	_	3.15	_	
Input voltage					6.0	4.2			4.2		V
input voitage					2.0			0.5	_	0.5	v
	Low-level	VIL			3.0			0.8	_	0.8	
	LOW-IEVEI	۷IL			4.5			1.35	_	1.35	
					6.0			1.8	_	1.8	
				GND	2.0		200		_		
		$R_{ON} = V_{I/O} = V_{CO}$ $V_{I/O} = 2 m/$ $V_{IN} = V_{ILO}$ $V_{I/O} = V_{CO}$	$V_{IN} = V_{IL} \text{ or } V_{IH}$	GND	3.0		45	86	_	108	Ω
				GND	4.5		24	37	_	46	
ON resistance			1/0 - 2 11/4	-3.0	3.0		17	26	_	33	
ONTESISIANCE			$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{I/O} = V_{CC} \text{ or } V_{EE}$ $I_{I/O} = 2 \text{ mA}$	GND	2.0		28	73		84	
				GND	3.0		22	38	_	44	
				GND	4.5	_	17	27	_	31	
				-3.0	3.0	_	15	24	_	28	
				GND	2.0	_	10	25	_	35	Ω
Difference of O resistance betw		ABass	V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>I/O</sub> = V <sub>CC</sub> to V <sub>EE</sub>	GND	3.0	_	5	15	_	20	
switches	een		$V_{I/O} = 2 \text{ mA}$	GND	4.5	_	5	13	_	18	52
			1/U – 2 11A	-3.0	3.0	_	5	10	_	15	
Input/Output lea	akade		$V_{OS} = V_{CC} \text{ or } GND$	GND	3.0	_	_	±0.25	_	±2.5	
(switch OFF)		I <sub>OFF</sub>	$V_{IS} = GND \text{ to } V_{CC}$ $V_{IN} = V_{IL} \text{ or } V_{IH}$	-3.0	3.0	_	_	±0.5	_	±5.0	μA
Input/Output leakage		,	V <sub>OS</sub> = V <sub>CC</sub> or GND	GND	3.0			±0.25	_	±2.5	
current (switch ON, out	put open)	lin	$V_{IN} = V_{IL} \text{ or } V_{IH}$	-3.0	3.0	_	_	±0.5	_	±5.0	μA
Control input current		I <sub>IN</sub>	$V_{IN} = V_{CC}$ or GND	GND	6.0	_		±0.1	_	±0.1	μA
Outeeent	lu aumant			GND	3.0			4.0		40.0	•
Quiescent supp	by current	ICC	$V_{IN} = V_{CC}$ or GND	-3.0	3.0			8.0		80.0	μA

# AC Electrical Characteristics ( $C_L = 50 \text{ pF}$ , Input: $t_r = t_f = 3 \text{ ns}$ , GND = 0 V)

Characteristics	Symbol	Та	at Condition			-	Га = 25°С	)	Ta = −40~85°C		Unit
Characteristics	Symbol	Test Condition		$V_{\text{EE}}(V)$	$V_{CC}(V)$	Min	Тур.	Max	Min	Max	Unit
		All types		GND	2.0	_	3.2	6.0		6.9	ns
Phase difference between	φl/O			GND	3.0	_	1.8	3.0	_	3.5	
input and output	ψι/Ο			GND	4.5		1.3	1.8		2.1	
				-3.0	3.0	_	1.1	1.3		1.5	
				GND	2.0	_	9.0	17		20	
Output enable time	t <sub>pZL</sub>	Figure	1 (Note 1)	GND	3.0		5.7	9.0		11	ne
	t <sub>p</sub> ZH	rigure		GND	4.5		4.5	6.0		7.0	ns
				-3.0	3.0		5.8	8.0		10	
				GND	2.0	_	13.5	21		25	ns
Output disable time	t <sub>pLZ</sub>	Figure 1 (Not	1 (Note 1)	GND	3.0		11.3	15		18	
	t <sub>pHZ</sub>			GND	4.5	_	10.3	12		14	
				-3.0	3.0	_	10.9	13		15	
Control input capacitance	C <sub>in</sub>	All type	es (Note 2)	_	_	_	5	10		10	pF
		4051	Figure 2			_	11	25		25	
COMMON terminal capacitance	CIS	4052		-3.0	3.0		9	20	—	20	
	$ \begin{array}{c} t_{pZL} \\ t_{pZH} \\ t_{pZH} \\ \end{array} \\ \begin{array}{c} F_{igure 1} \\ F_{igure 1} \\ \end{array} \\ \begin{array}{c} (Note 1) \\ G \\ $				7	15		15	1		
		4051	Eiguro 2			)	6	13		13	
SWITCH terminal capacitance	C <sub>OS</sub>	4052	J	-3.0	3.0		6	13	—	13	pF
		4053					6	13		13	
		4051					3	6		6	
Feedthrough capacitance	C <sub>IOS</sub>	4052		-3.0	3.0	—	- 3 6	—	6	pF	
		4053	· · · · ·				3	6		6	
		4051	Figure 2 (Note 3)				14	_	1		pF
Power dissipation capacitance	C <sub>PD</sub>	4052		GND	6.0	—	24		—	—	
		4053	, , ,				18				

Note 1:  $R_L = 1 \ k\Omega$ 

Note 2:  $C_{in}$ ,  $C_{IS}$ ,  $C_{OS}$  and  $C_{IOS}$  are guaranteed by the design.

Note 3: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance of IC which is calculated from the operating current consumption without load.

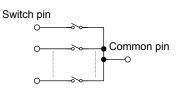
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

# \*Analog Switch Characteristics (GND = 0 V, Ta = 25°C)

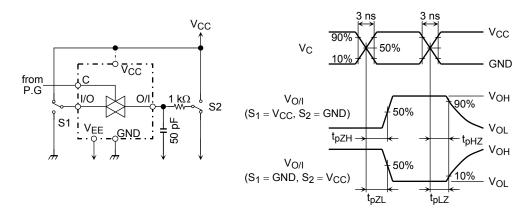
Characteristics	Symbol	Test Condition	_		Typ.	Unit	
Characteristics	Symbol	Test Condition		$V_{EE}(V)$	V <sub>CC</sub> (V)	тур.	Onic
			$V_{IN} = 2.0 V_{p-p}$	0	3.0	0.100	
Sine Wave Distortion (T.H.D)		$R_L = 10 k\Omega, C_L = 50 pF,$ f <sub>IN</sub> = 1 kHz	$V_{IN} = 4.0 V_{p-p}$	0	4.5	0.030	%
			V <sub>IN</sub> = 6.0 V <sub>p-p</sub>	-0.3	3.0	0.020	
			4051			150	MHz
			4052	0	3.0	180	
		Adjust f <sub>IN</sub> voltage to obtain 0dBm at V <sub>OS</sub> .	4053			200	
		Increase f <sub>IN</sub> frequency until dB	4051			150	
Frequency response (switch ON)	f <sub>max</sub>	meter reads -3dB.	4052	0	4.5	180	
(Switch ON)		$R_L = 50 \Omega$ , $C_L = 10 pF$ , $f_{IN} = 1 MHz$ , sine wave	4053			200	
		Figure 3	4051		3.0	150	
			4052	-3.0		180	
			4053			200	
		$V_{IN}$ is centered at $(V_{CC} - V_{EE})/2$ .	0	3.0	-45	dB	
		Adjust input for 0dBm.		0	4.5		45
		$R_L=600~\Omega,~C_L=50~pF,~f_{IN}=1~M$	-	4.5	-40		
Feed through attenuation (switch OFF)		Figure 4	-3.0	3.0	-45		
· · · ·				0	3.0	-60	
		$R_L$ = 50 $\Omega$ , $C_L$ = 10 pF, $f_IN$ = 1 MH	50 $\Omega$ , C <sub>L</sub> = 10 pF, f <sub>IN</sub> = 1 MHz, sine wave		4.5	-60	1
				-3.0	3.0	-60	
Crosstalk		$R_L = 600 \ \Omega$ , $C_L = 50 \ pF$ , $f_{IN} = 1 \ M$	Hz, square wave	0	3.0	90	
(control input to signal	(4		$(t_r = t_f = 6 \text{ ns})$			150	mV
output)		Figure 5		-3.0	3.0	-45 -45 -45 -60 -60 -60 90	
Crosstalk		Adjust V <sub>IN</sub> to obtain 0dBm at input	0	3.0	-45		
(between any switches)		$R_L=600~\Omega,~C_L=50~pF,~f_{IN}=1~M$	0	4.5	-45	dB	
(Detween any Switches)		Figure 6		-3.0	3.0	-45	

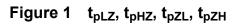
\*: These characteristics are determined by design of devices.



# <u>TOSHIBA</u>

### **AC Test Circuit**





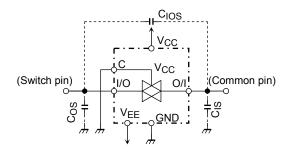
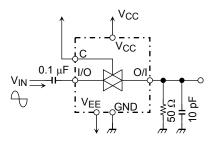


Figure 2 C<sub>IOS</sub>, C<sub>IS</sub>, C<sub>OS</sub>





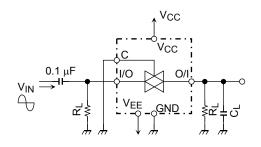
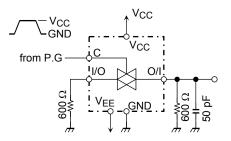
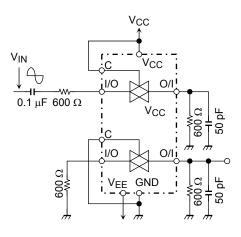


Figure 4 Feedthrough





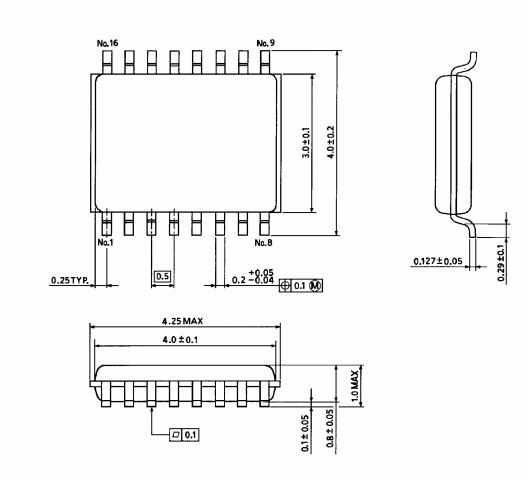




### **Package Dimensions**

VSSOP16-P-0030-0.50

Unit : mm



Weight: 0.02 g (typ.)

#### **RESTRICTIONS ON PRODUCT USE**

20070701-EN GENERAL

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
   In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.).These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patents or other rights of TOSHIBA or the third parties.
- Please contact your sales representative for product-by-product details in this document regarding RoHS compatibility. Please use these products in this document in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses occurring as a result of noncompliance with applicable laws and regulations.